

1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability ($T_{j(max)} = 175\text{ °C}$)

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

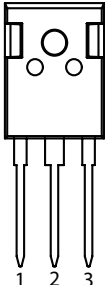
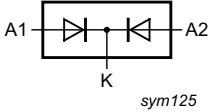
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		1200			V
$I_{O(AV)}$	limiting average output current	$\delta = 0.5$; $T_{mb} \leq 129\text{ °C}$; square-wave pulse; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 ; Fig. 4	20			A
T_j	junction temperature		175			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10\text{ A}$; $T_j = 25\text{ °C}$; per diode; Fig. 6	-	1.4	1.6	V
		$I_F = 10\text{ A}$; $T_j = 150\text{ °C}$; per diode; Fig. 6	-	1.85	2.3	V
		$I_F = 10\text{ A}$; $T_j = 175\text{ °C}$; per diode; Fig. 6	-	2	2.6	V
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10\text{ A}$; $V_R = 400\text{ V}$; $dI_F/dt = 500\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; per diode; Fig. 8	-	24	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	K	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
GKTSC201200CW	TO247	GKTSC201200CWQ	Tube	30	TO247N	20-Jul-2015

7. Marking

Table 4. Marking codes

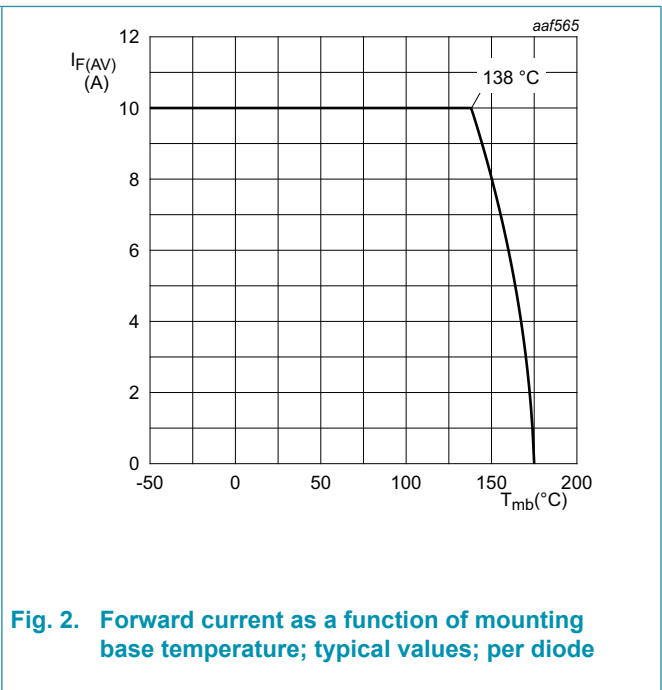
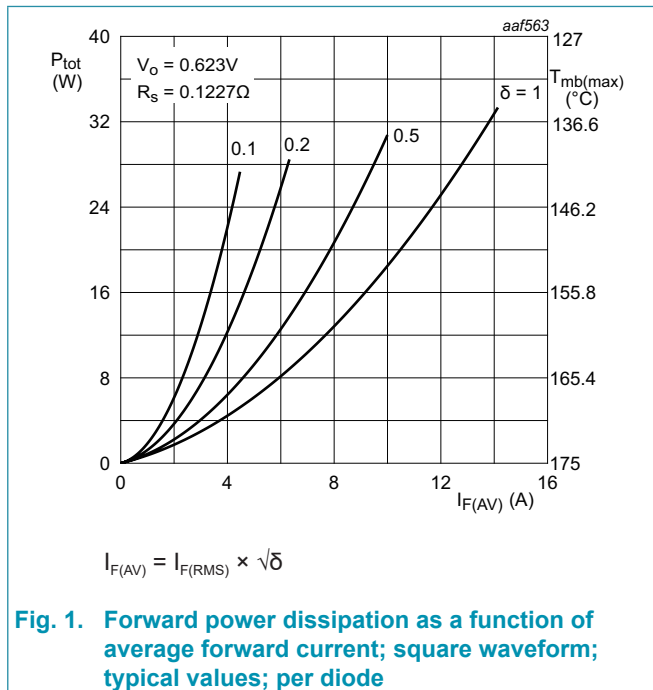
Type number	Marking codes
GKTSC201200CW	GKTSC201200CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V_R	reverse voltage	DC	1200	V
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25 \mu s$; $T_{mb} \leq 138 \text{ }^\circ\text{C}$; square-wave pulse; per diode	20	A
$I_{O(AV)}$	limiting average output current	$\delta = 0.5$; $T_{mb} \leq 129 \text{ }^\circ\text{C}$; square-wave pulse; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3 ; Fig. 4	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10 \text{ ms}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; sine-wave pulse; per diode	110	A
		$t_p = 10 \mu s$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; sine-wave pulse; per diode	720	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; $t_p = 10 \text{ ms}$; per diode	61	A^2s
T_{stg}	storage temperature		-55 to 175	$^\circ\text{C}$
T_j	junction temperature		175	$^\circ\text{C}$



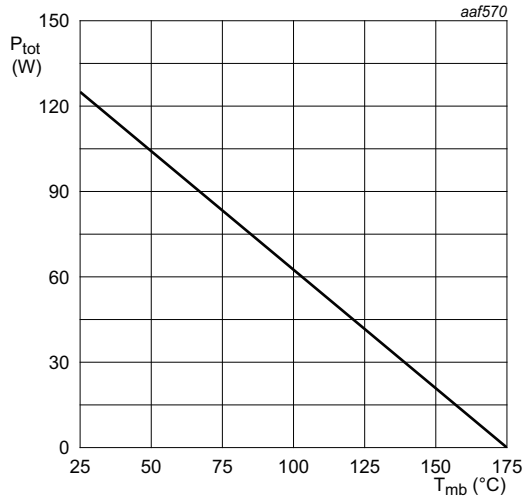


Fig. 3. Total power dissipation as a function of mounting base temperature; per diode

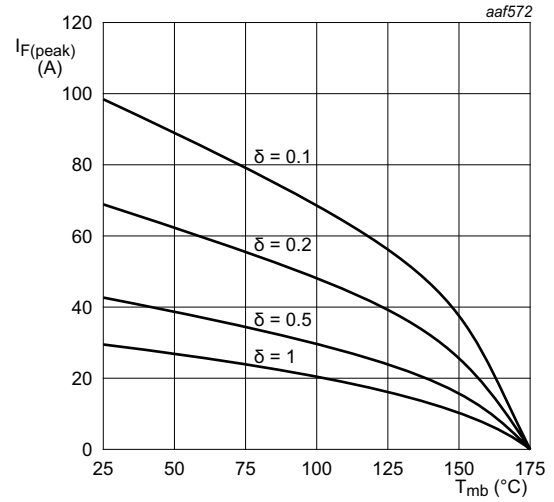


Fig. 4. Current derating as a function of mounting base temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	per diode; Fig. 5	-	-	1.2	K/W
		both diodes conducting	-	-	0.75	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W

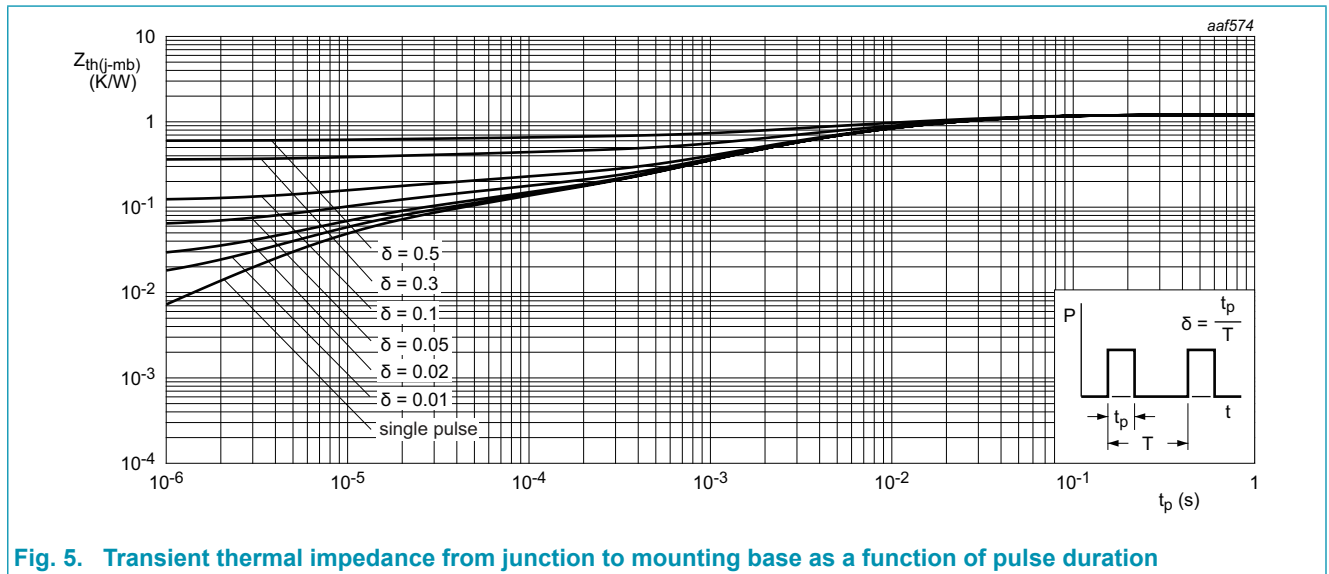
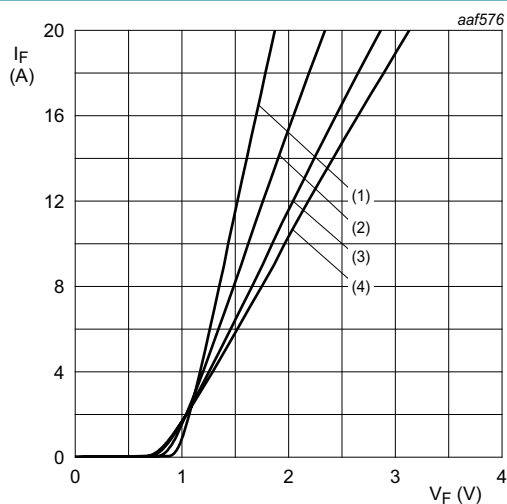


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward current	$I_F = 10 \text{ A}; T_J = 25 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.4	1.6	V
		$I_F = 10 \text{ A}; T_J = 150 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.85	2.3	V
		$I_F = 10 \text{ A}; T_J = 175 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	2	2.6	V
I_R	reverse current	$V_R = 1200 \text{ V}; T_J = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	10	110	μA
		$V_R = 1200 \text{ V}; T_J = 175 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	450	-	μA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_J = 25 \text{ }^\circ\text{C};$ per diode; Fig. 8	-	24	-	nC
C_d	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	510	-	pF
		$f = 1 \text{ MHz}; V_R = 400 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	48	-	pF
		$f = 1 \text{ MHz}; V_R = 800 \text{ V}; T_J = 25 \text{ }^\circ\text{C}$	-	41	-	pF



- (1) $T_J = 25 \text{ }^\circ\text{C};$ typical values
- (2) $T_J = 100 \text{ }^\circ\text{C};$ typical values
- (3) $T_J = 150 \text{ }^\circ\text{C};$ typical values
- (4) $T_J = 175 \text{ }^\circ\text{C};$ typical values

Fig. 6. Forward current as a function of forward voltage; typical values; per diode

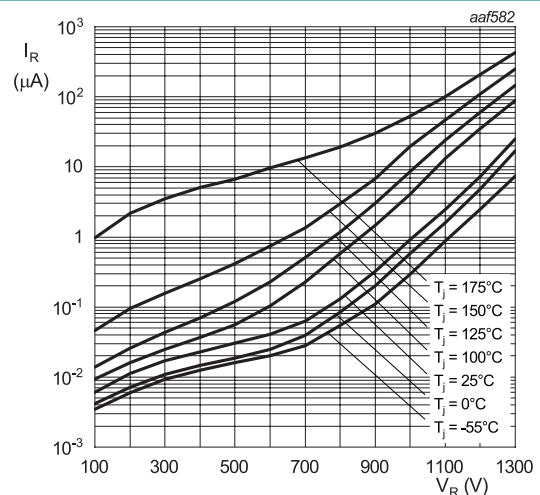


Fig. 7. Reverse leakage current as a function of reverse voltage; typical value; per diode

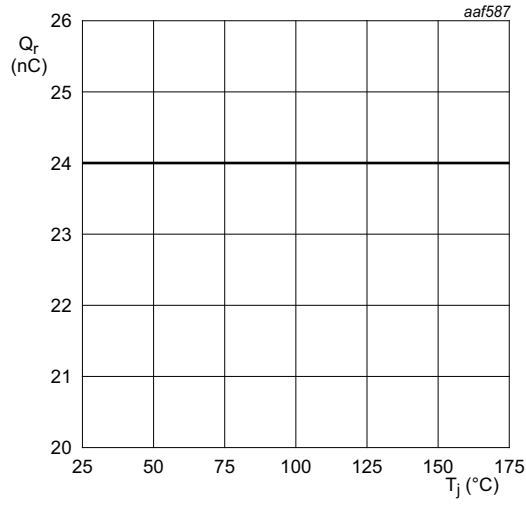
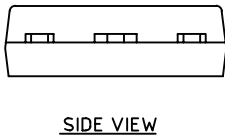
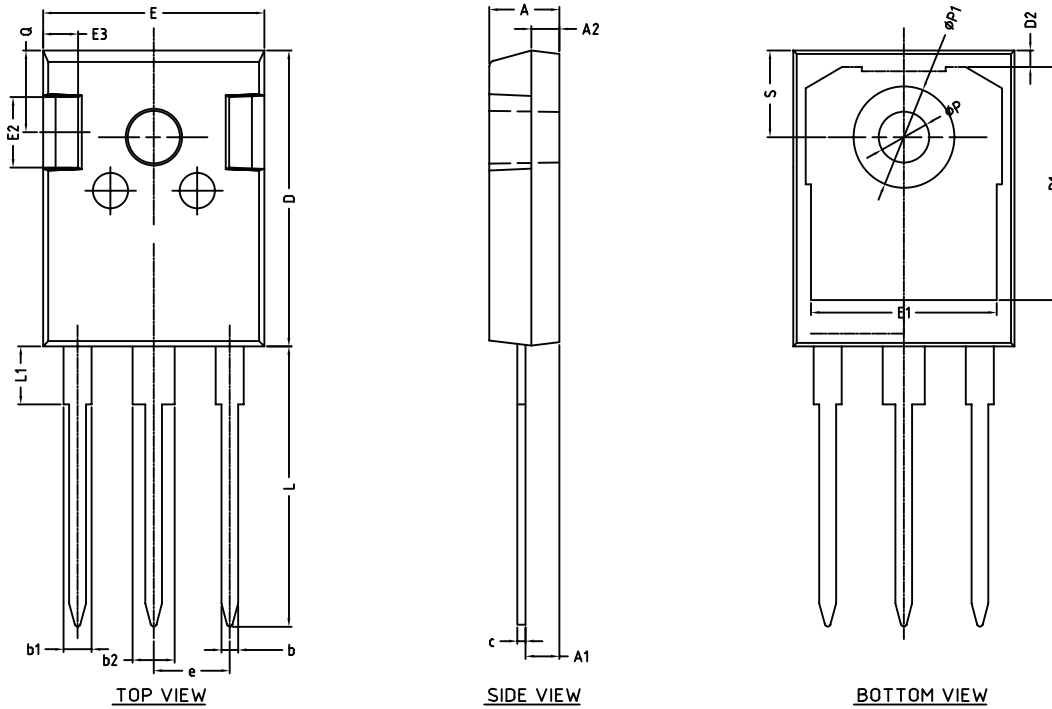


Fig. 8. Recovered charge as a function of junction temperature; per diode

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247

SOT429N



UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	MAX	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	20.10	4.75	3.70	7.40	6.00	6.25
	MIN	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40	19.80	-	3.50	-	5.60	6.05

OUTLINE VERSION	REFERENCES			PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT429N		TO-247			

IMPORTANT NOTICE – PLEASE READ CAREFULLY

SZGKT Microelectronics NV and its subsidiaries reserve the right to make changes, corrections, enhancements, modifications, and improvements to SZGKT.